Appl. No.: 10/706,862

Amendment Dated September 16, 2005 Reply to Office Action of June 20, 2005

Amendments to the Claims:

1. (currently amended) A composition for forming porous film, the composition consisting essentially of siloxane polymer and one or more quaternary ammonium salts represented by following formula (1) or (2):

$$[(R^1)_4N]^+[R^2X]^-$$
 (1)

$$H_k[(R^1)_4N]_m^+Y^{n-}$$
 (2)

wherein R¹ independently represents a straight chain or branched alkyl or aryl group having 1 to 10 carbons which may have a substituent and R¹s may be same or different; R² represents a hydrogen atom or an straight chain or branched alkyl or aryl group having 1 to 10 carbons which may have a substituent; X represents CO₂, OSO₃ or SO₃; Y represents SO₄, SO₃, CO₃, O₂C-CO₂, NO₃ or NO₂; and k is 0 or 1, m is 1 or 2 and n is 1 or 2 in proviso that n=1 requires k=0 and m=1, and n=2 requires k=0 and m=2, or k=1 and m=1, and wherein the one or more quaternary ammonium salts are present in an amount of 0.001 to 10 parts by weight per one part by weight of the siloxane polymer.

- 2. (original) The composition for forming porous film according to Claim 1 wherein said siloxane polymer has a weight-average molecular weight of 10,000 to 1,000,000 using polyethylene as a standard.
- 3. (previously presented) A method for forming porous film comprising steps of applying said composition of Claim 1 on a substrate to form a film and heating the film.
 - 4. (previously presented) A porous film obtained from said composition of Claim 1.
- 5. (previously presented) An interlevel insulator film formed by said composition of Claim 1.
- 6. (currently amended) A semiconductor device comprising internal porous film which is formed by

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applying on a substrate a composition for forming porous film consisting essentially of siloxane polymer and one or more quaternary ammonium salts represented by following formula (1) or (2):

$$[(R^1)_4N]^+[R^2X]^-$$
 (1)

$$H_k[(R^1)_4N]_m^+Y^{n-}$$
 (2)

wherein R¹ independently represents a straight chain or branched alkyl or aryl group having 1 to 10 carbons which may have a substituent and R¹s may be same or different; R² represents a hydrogen atom or an straight chain or branched alkyl or aryl group having 1 to 10 carbons which may have a substituent; X represents CO₂. OSO₃ or SO₃; Y represents SO₄, SO₃, CO₃, O₂C-CO₂, NO₃ or NO₂; and k is 0 or 1, m is 1 or 2 and n is 1 or 2 in proviso that n=1 requires k=0 and m=1, and n=2 requires k=0 and m=2, or k=1 and m=1, and wherein the one or more quaternary ammonium salts are present in an amount of 0.001 to 10 parts by weight per one part by weight of the siloxane polymer;

and heating.

- 7. (original) The semiconductor device according to Claim 6 wherein said siloxane polymer has a weight-average molecular weight between 10,000 and 1,000,000 using polyethylene as a standard.
- 8. (previously presented) The semiconductor device according to Claim 6 wherein said porous film is between metal interconnections in a same layer of multi-level interconnects, or is between upper and lower metal interconnection layers.